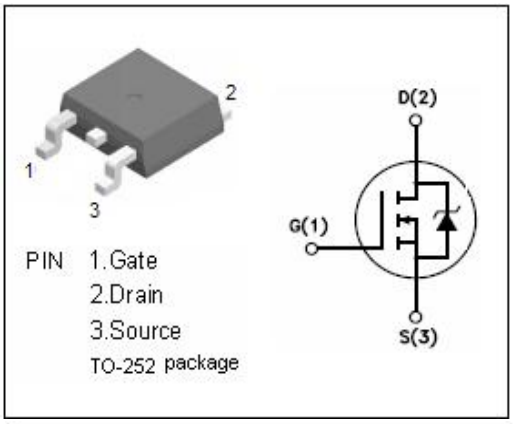
Isc N-Channel MOSFET Transistor IXFY36N20X3

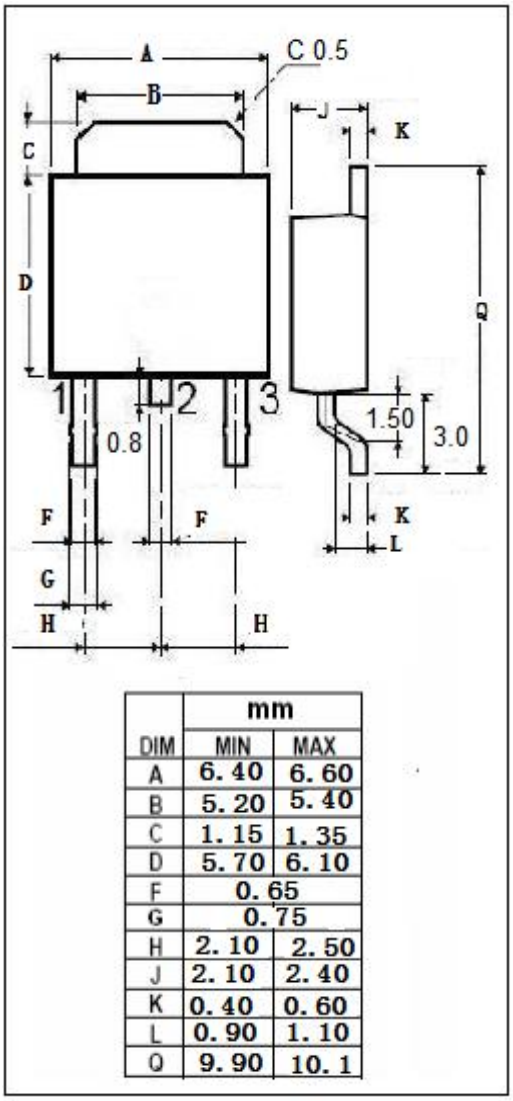


• FEATURES

- With To-252(DPAK) package
- Low input capacitance and gate charge
- Low gate input resistance
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• APPLICATIONS

- Switching applications



DIM	mm MIN	MAX
A	6.40	6.60
B	5.20	5.40
C	1.15	1.35
D	5.70	6.10
F	0.65	
G	0.75	
H	2.10	2.50
J	2.10	2.40
K	0.40	0.60
L	0.90	1.10
Q	9.90	10.1

• ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	200	V
V_{GSS}	Gate-Source Voltage	±30	V
I_D	Drain Current-Continuous	36	A
I_{DM}	Drain Current-Single Pulsed	145	A
P_D	Total Dissipation @T_C=25℃	170	W
T_{ch}	Max. Operating Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	0.73	℃/W

Download from alldatasheet.com

Isc N-Channel MOSFET Transistor IXFY36N20X3

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V; I_D= 0.25mA	200			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}; I_D=0.5mA	2.5		4.5	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}= 10V; I_D=18A		38	45	mΩ
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V;V_{DS}= 0V			±0.1	μA
I_{DSS}	Drain-Source Leakage Current	V_{DS}=200V; V_{GS}= 0V			5	μA
V_{SDF}	Diode forward voltage	I_{SD}=36A, V_{GS} = 0 V			1.4	V

Download from alldatasheet.com